

Public Products List

PCI Title : SEA05TR : Metal mask change

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Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

SEA05TR

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Reliability Report

General Information		Locations
Product Line		Wafer fab location CATANIA
Product Description	CONTROLLER	Assembly plant location CARSEM M
Product division	I&PC	Malaysia
Package	SOT23 6L	
Silicon process technology	BCD6S	Reliability assessment Pass

DOCUMENT HISTORY

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<u>1</u> APPLICABLE AND REFERENCE DOCUMENTS

Document reference	Short description
AEC-Q100 8161393A	Stress test qualification for integrated circuitsGeneral Specification For Product Development



2 RELIABILITY EVALUATION OVERVIEW

2.1 Objectives

This report contains the reliability evaluation performed on the U1M7 device diffused in CATANIA and assembled in SOT23 6L in CARSEM M Malaysia.

Considering that U1M7 device is an option of the already qualified UQ23 device (see report RR001609CS2047) and this option is marginal from reliability point of view, all positive results obtained from UQ23 can be extended by similarity to U1M7.

According to Reliability Qualification Plan, below is the list of the trials performed on reference device:

Die Oriented Tests (performed on UQ23)

- High Temperature Operating Life
- High Temperature Reverse Bias

Package Oriented Tests (performed on equivalent Test Vehicle)

- Preconditioning
- Temperature Cycling
- Autoclave
- High Temperature Storage

Electrical Characterization (performed on UQ23)

- ESD resistance test
- LATCH-UP resistance test

2.2 Conclusion

Taking in account the results of the trials performed the U1M7 diffused in CATANIA and assembled in SOT23 6L in CARSEM M Malaysia can be qualified from reliability viewpoint.



<u>3 DEVICE CHARACTERISTICS</u>

3.1 Device description

3.1.1 Pin connection



3.1.2 Block diagram





3.1.3 Bonding diagram





3.1.4 Package outline/Mechanical data

Dim		mm.			inch	
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.
Α		0.9	1.45		0.035	0.057
A1		0	0.1		0	0.0039
A2		0.9	1.3		0.035	0.0512
b		0.35	0.5		0.014	0.02
с		0.09	0.2		0.004	0.008
D		2.8	3.05		0.11	0.120
E		1.5	1.75		0.059	0.0689
е	0.95			0.037		
Н		2.6	3		0.102	0.118
L		0.1	0.6		0.004	0.024
θ (degrees)		0°	10°		0°	10°









Traceability

Wafer fab information			
Wafer fab manufacturing location	CATANIA		
Wafer diameter	8 inches		
Wafer thickness	280µm		
Silicon process technology	BCD6S		
Die finishing back side	Cr/Ni/Au		
Die size	874 X 805µm		
Bond pad metallization layers	Ti/AICu/TiNARC		
Passivation	TEOS/SiN/Polyimide		
Metal levels	3		

Assembly Information			
Assembly plant location	CARSEM M Malaysia		
Package description	SOT23 6L		
Die pad size	0.981 X 1.626mm		
Molding compound	CEL8240 HF10LXC		
Wires bonding materials/diameters	Au / 1mils		
Die attach material	QMI519		
Lead solder material	Sn		



4 TESTS RESULTS SUMMARY

4.1 Test plan and results summary

Die Oriented Tests

Test	Test short description (performed on UQ23)					
	Method	Conditions	Sample/	Lot	Duration	Results
			LOtS	ND		Faii/55
HTRB	High Temperature Reverse Bias					
		Tj=150°C Vin=36V,Vcc=6V,Vboot=42V	77	1	1000h	0/77
HTOL	High Temperature Operating Life					
	On chip-board	Tj=150°C	77	1	1000h	0/77
		Vcc=5V, Vin=21V				

Package Oriented Tests

Test	Test short description (performed on equivalent Test Vehicle)					
	Method	Conditions	Sample/	Lot	Duration	Results
			Lots	Nb		Fail/SS
PC	Pre-Conditioning: N	loisture sensitivity level 1				
		168h 85°C/85% - 3 reflow PBT 260°C	100	1		0/100
AC	Autoclave					
	PC before	121°C 2atm	50	1	168h	0/50
тс	Temperature Cycling					
	PC before	Temp. range: -50/+150°C	50	1	1000cy	0/50
HTSL	High Temperature Storage Life					
	No bias	Tamb=150°C	50	1	1000h	0/50

Electri	Electrical Characterization Tests (performed on UQ23)					
Test	Method	Conditions	Sample/ Lots	Number of lots	Duration	Results Fail/SS
ESD	Electro Static Discharge					
	Human Body Model	+/- 5000V	3	1		0/3
	Machine Mode	+/ 200V	3	1		0/3
	Charge Device Model	+/ 1500V	3	1		0/3
LU	Latch-Up					
	Over-voltage and Current Injection	Tamb=85°C Jedec78 – Level B	3	1		0/3



5 TESTS DESCRIPTION & DETAILED RESULTS

5.1 Die oriented tests

5.1.1 High Temperature Operating Life

This test is performed like application conditions in order to check electromigration phenomena, gate oxide weakness and other design/manufacturing defects put in evidence by internal power dissipation.

The flow chart is the following:

- Initial testing @ Ta=25°C
- Check at 168 and 500hrs @ Ta=25°C
- Final Testing (1000 hr.) @ Ta=25°C

5.1.2 High Temperature Reverse Bias

This test is performed to evaluate die problems related with chip stability, layout structure, surface contamination and oxide faults.

The flow chart is the following:

- Initial testing @ Ta=25°C
- Check @ 168 and 500hrs @ Ta=25°C
- Final Testing @ 1000hrs @ Ta=25°C

5.2 Package oriented tests

5.2.1 Pre-Conditioning

The device is submitted to a typical temperature profile used for surface mounting, after a controlled moisture absorption.

The scope is to verify that the surface mounting stress does not impact on the subsequent reliability performance. The typical failure modes are "pop corn" effect and delamination.

5.2.2 High Temperature Storage Life

The device is stored in unbiased condition at the max. temperature allowed by the package materials, sometimes higher than the max. operative temperature.

The scope is to investigate the failure mechanisms activated by high temperature, typically wire-bonds solder joint ageing, data retention faults, metal stress-voiding

5.2.3 Thermal Cycles

The purpose of this test is to evaluate the thermo mechanical behavior under moderate thermal gradient stress. Test flow chart is the following:

- Initial testing @ Ta=25°C.
- Readout @ 500 cycles.
- Final Testing @ 1000 cycles @ Ta=25°C.

TEST CONDITIONS:

- Ta= -50°C to +150°C(air)
- 15 min. at temperature extremes
- 1 min. transfer time

5.2.4 Autoclave

The purpose of this test is to point out critical water entry path with consequent corrosion phenomena related to chemical contamination and package hermeticity.

- Test flow chart is the following:
 - Initial testing @ Ta=25°C.
 - Final Testing (168hrs) @ Ta=25°C.

TEST CONDITIONS:

- P=2.08 atm
- Ta=121°C
- test time= 168 hrs



5.3 Electrical Characterization Tests

5.3.1 Latch-up

This test is intended to verify the presence of bulk parasitic effects inducing latch-up.

The device is submitted to a direct current forced/sinked into the input/output pins. Removing the direct current no change in the supply current must be observed.

Stress applied:

condition	NEG. INJECTION	POS. INJECTION	OVERVOLTAGE
IN low: 0V	-100mA	Inom+100mA	Vcc=54V
IN high: 3.3V	-100mA	Inom+100mA	Vcc=54V

5.3.2 E.S.D.

This test is performed to verify adequate pin protection to electrostatic discharges. The flow chart is the following:

- Initial testing @ Ta=25°C
- ESD discharging @ Ta=25°C
- Final Testing @ Ta=25°C

TEST CONDITIONS:

0	Human Body Model	JEDEC STANDARD JESD22-A114 CDF-AEC-Q100-002
0	Machine Model	JEDEC STANDARD EIA/JESD-A115 CDF-AEC-Q100-003

 Charge Device Model
ANSI/ESD STM 5.3.1 ESDA CDF-AEC-Q100-011